Boron in Silicon implant

Depth vs. Y-Axis

- + 1750 A
- -1750 A
- Layer 1
- 0 A — Target Depth — 3500 A
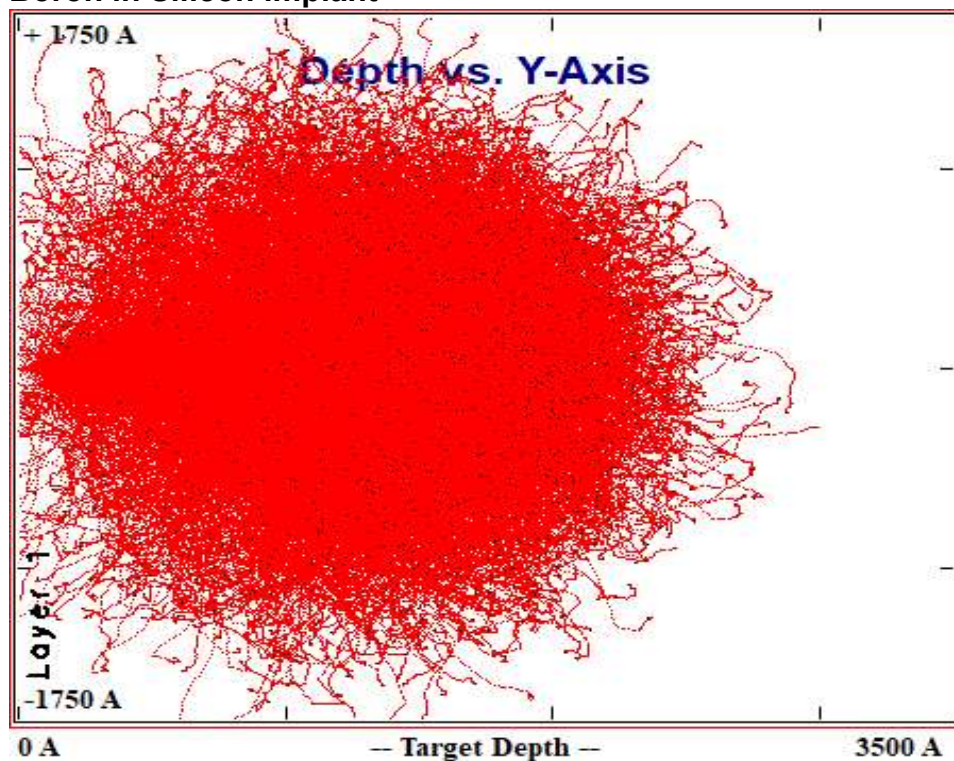
9999 Ions Calculated

Ion Type = B
Ion Energy = 40 keV
Ion Angle = 0

Calculation Parameters:

Backscattered Ions	80
Transmitted Ions	1
Vacancies/Ion	299.5

ION STATS

	Range	Straggle
Longitudinal	1454 A	486 A
Lateral Proj.	443 A	551 A
Radial	691 A	345 A

Type of Damage Calculation
  Quick: Kinchin-Pease

Stopping Power Version
  SRIM-2008

% ENERGY	LOSS Ions	Recoils
Ionization	63.07	7.97
Vacancies	0.25	1.24
Phonons	0.87	26.60

SPUTTERING YIELD

	Atoms/Ion	eV/Atom
TOTAL		
Si	0.000000	0.00

Target layers:

	Layer Name	Width (A)	Density	Si (28.086)	Solid/Gas	Stop Corr.
1	Layer 1	3000	2.321	1.00000	Solid	1
	Lattice Binding Energy			2		
	Surface Binding Energy			4.7		
	Displacement Energy			15		